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Amendments to the Claims

Please cancel claims 3-4, add new claim 21, and amend the remaining claims as follows:

1. (Currently Amended) A method for fabricating a capacitor in a metal/insulator/metal structure including a first metal layer, a dielectric layer, and a second metal layer, the method comprising:

etching the second metal layer ~~and the dielectric layer in order~~; and

~~changing the etching conditions associated with the second metal layer prior to~~ etching the dielectric layer under conditions different from etching the second metal layer, to leave a residual dielectric layer over the first metal layer in an etched part of the dielectric layer.

2. (Currently Amended) The method of claim 1, wherein etching the second metal layer ~~and the dielectric layer~~ comprises ~~using~~ a first reactive ion etching process, and etching the dielectric layer comprises a second reactive ion etching process.

3. (Cancelled)

4. (Cancelled)

5. (Currently Amended) The method of claim 1, wherein[[,]] etching the second metal layer includes etching using a mixture gas consisting essentially of Cl_2, CHF_3 and Ar, and

wherein etching the dielectric layer includes etching using a mixture gas consisting essentially of Cl_2 and Ar.

6. (Original) The method of claim 1, wherein the second metal layer includes Ti and TiN stacked in order.

7. (Original) The method of claim 6, wherein a thickness of the Ti is 300 to 700Å and a thickness of the TiN is 1300 to 1700Å .

8. (Original) The method of claim 1, wherein a total thickness of the second metal layer is 1600 to 2400Å .

9. (Currently Amended) The method of claim 1, wherein the dielectric layer ~~is made of~~ comprises a nitride.

10. (Original) The method of claim 1, wherein a thickness of the dielectric layer is 400 to 800Å .

11. (Currently Amended) The method of claim 1, wherein the first metal layer comprises a first Ti/TiN ~~stacking structure~~, an AlCu layer and a second Ti/TiN ~~stacking structure, which are formed~~ in order.

12. (Currently Amended) The method of claim 1, wherein etching the second metal layer comprises using a mixture gas consisting essentially of Cl_2, CHF_3 and Ar in ~~the~~ a ratio of 5:1:5.

13. (Original) The method of claim 1, wherein, etching the second metal layer comprises etching the second metal layer for 45 to 55 seconds

14. (Original) The method of claim 1, wherein etching the second metal layer comprises generating a plasma at a pressure of 8mTorr and a power of 900W and applying a bias power of more than 150W.

15. (Currently Amended) The method of claim 1, wherein etching the dielectric layer comprises using a mixture gas consisting essentially of Cl_2 and Ar in ~~the~~ a ratio of 1 to 2.

16. (Original) The method of claim 1, wherein an etching time associated with the dielectric layer is between about 10 to 15% of an etching time associated with the second metal layer

17. (Original) The method of claim 1, wherein etching the dielectric layer comprises etching the dielectric layer for 4.5 to 8 seconds.

18. (Original) The method of claim 1, wherein etching the dielectric layer comprises generating a plasma is generated under a pressure of 8mTorr and an application power of 900W and applying a bias power of more than 150W.

19. (Currently Amended) The method of claim 1, ~~wherein~~further comprising, before etching the second metal layer ~~is etched~~, forming a photoresist pattern ~~is formed~~ on the second metal layer, and the second metal layer and the dielectric layer are etched using the photoresist pattern as a mask.

20. (Currently Amended) The method of claim ~~19~~ 1, wherein a thickness of the photoresist pattern is 11,000 to 15,000Å .

21. (New) The method of claim 1, wherein the dielectric layer comprises silicon nitride.

22. (New) The method of claim 1, wherein the residual dielectric layer comprises a continuous residual dielectric layer over the first metal layer.